



# ACE7310M

## N-Channel 30-V (D-S) MOSFET

### Description

The ACE7310M uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a kelvin connection to the source, which may be used to bypass the source inductance.

### Features

- Low  $r_{DS(on)}$  trench technology
- Low thermal impedance
- Fast switching speed

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ (m $\Omega$ )	$I_D$ (A)
30	5.5 @ $V_{GS} = 10V$	21
	7.8 @ $V_{GS} = 4.5V$	17

### Applications

- DC/DC Conversion
- Power Routing
- Motor Drives

### Absolute Maximum Ratings

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>a</sup>	$I_D$	$T_A=25^\circ C$	21
		$T_A=70^\circ C$	17.2
Pulse Drain Current <sup>b</sup>	$I_{DM}$	80	A
Continuous Drain Current (Diode Continuous) <sup>a</sup>	$I_S$	4.7	A
Power Dissipation <sup>a</sup>	$P_D$	$T_A=25^\circ C$	3.5
		$T_A=70^\circ C$	2
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	$t \leq 10sec$	35
		Steady State	81

#### Notes

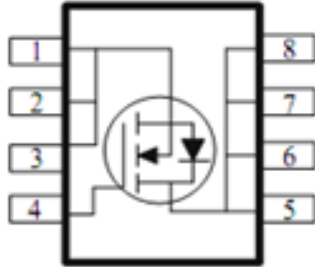
a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature



## Packaging Type

DFN3\*3-8L

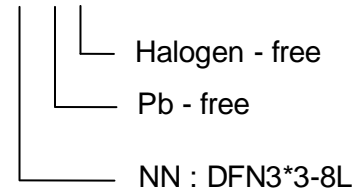


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## Ordering information

ACE7310M XX + H



## Electrical Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1			V
Gate Body Leakage	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$			1	uA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$			25	
On-State Drain-Current <sup>a</sup>	$I_{D(on)}$	$V_{DS}=5V, V_{GS}=10V$	30			A
Static Drain-Source On-Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS}=10V, I_D=18.2A$			5.5	mΩ
		$V_{GS}=4.5V, I_D=14.6A$			7.8	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS}=15V, I_D=18.2A$		20		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S=2.3A, V_{GS}=0V$		0.81		V
Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	$V_{DS}=15V, V_{GS}=4.5V, I_D=18.2A$		19		nC
Gate-Source Charge	$Q_{gs}$			9.8		
Gate-Drain Charge	$Q_{gd}$			8.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=15V, R_L=0.82\Omega, I_D=18.2A, V_{GEN}=10V, R_{GEN}=6\Omega,$		12		ns
Rise Time	$t_f$			11		
Turn-Off Delay Time	$t_{d(off)}$			53		
Fall Time	$t_f$			16		
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V, f=1MHz$		2677		pF
Output Capacitance	$C_{oss}$			304		
Reverse Transfer Capacitance	$C_{rss}$			188		

Note:

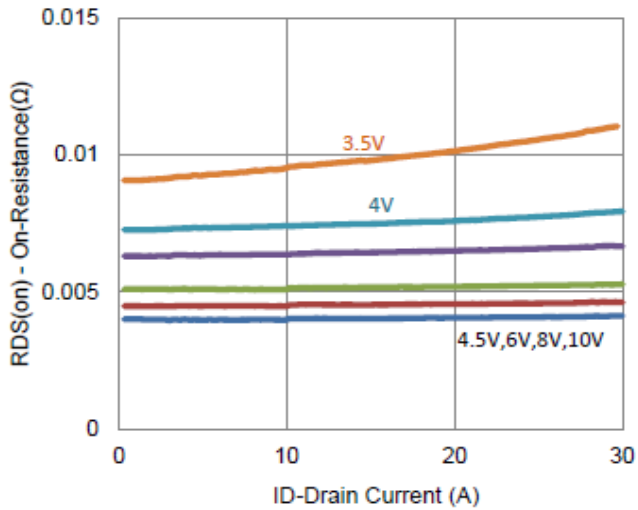
- a. Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.



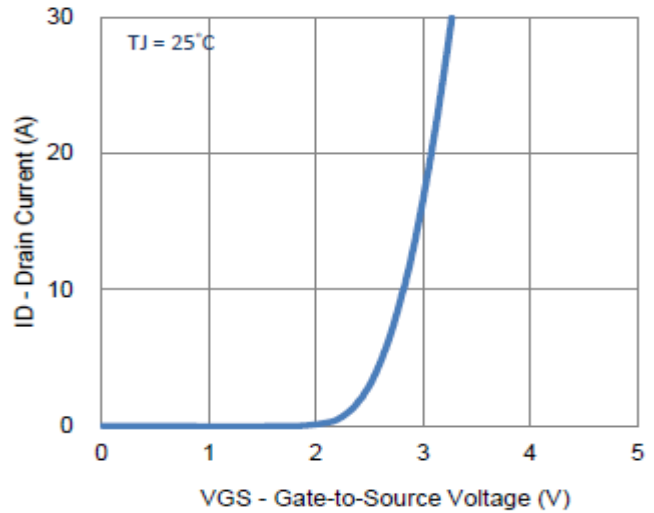
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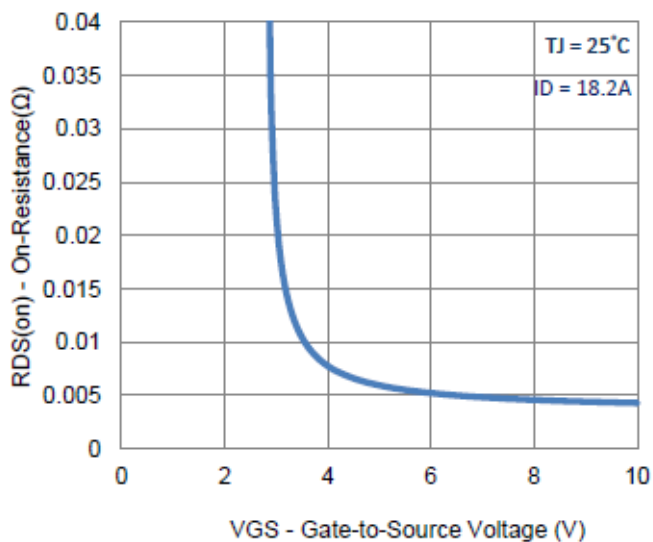
### Typical Electrical Characteristics



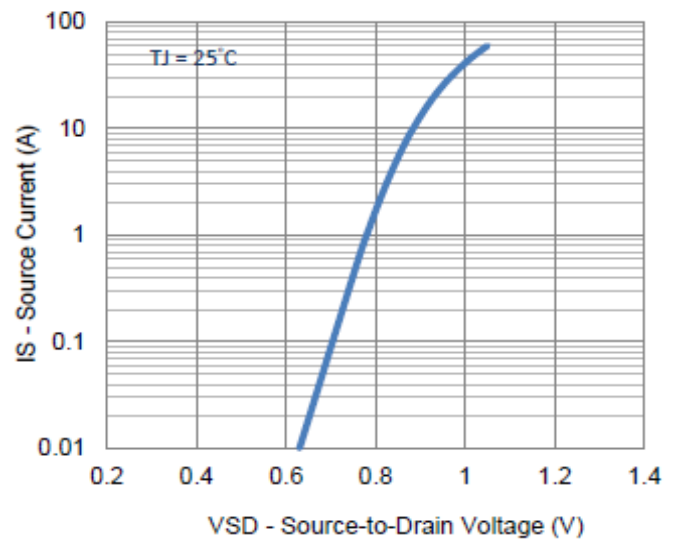
1. On-Resistance vs. Drain Current



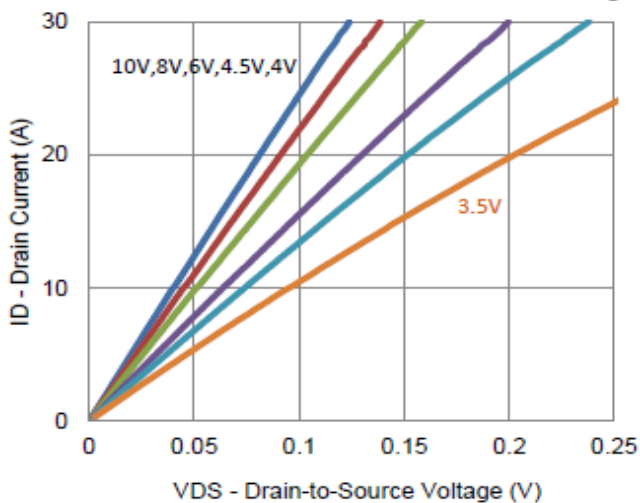
2. Transfer Characteristics



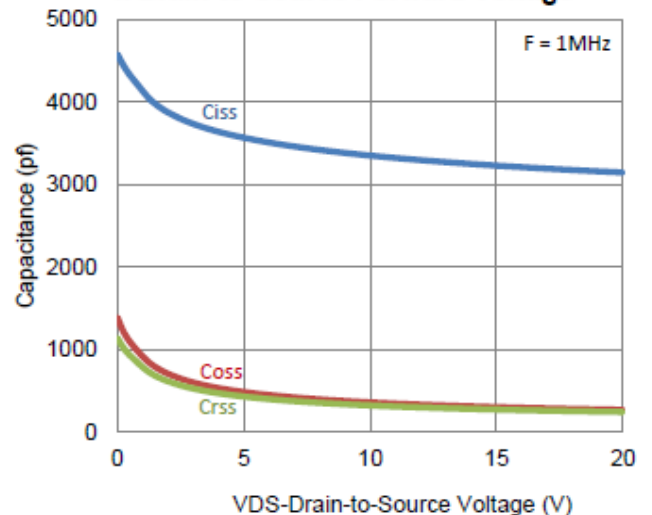
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics

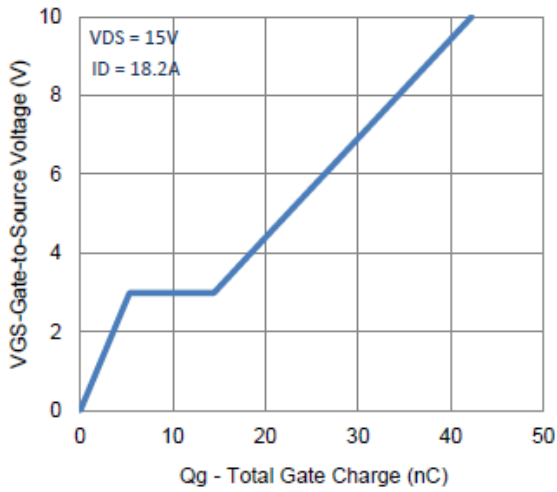


6. Capacitance

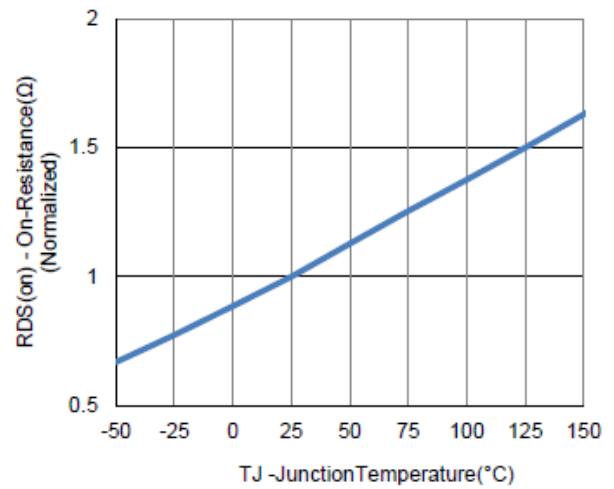


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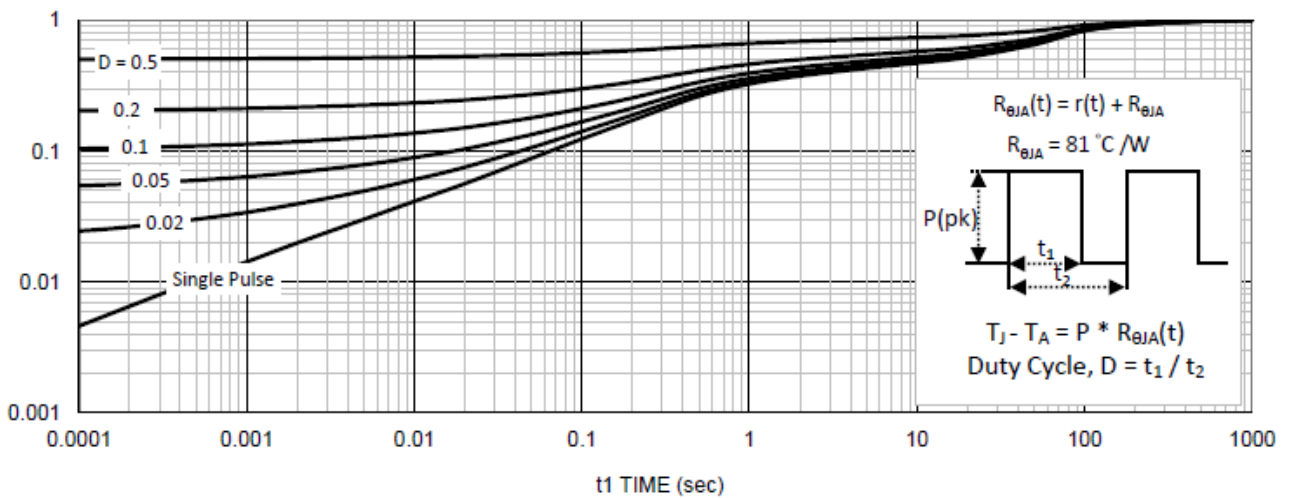
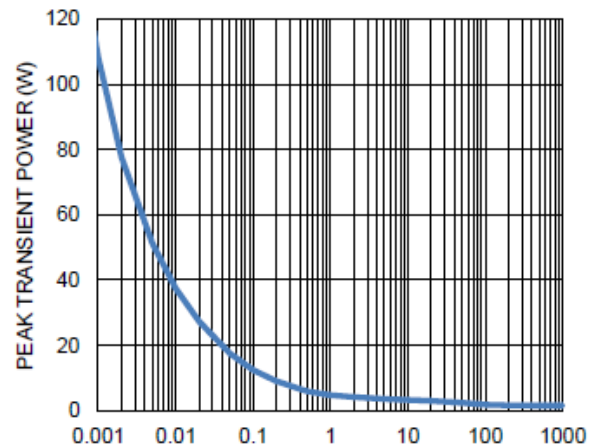
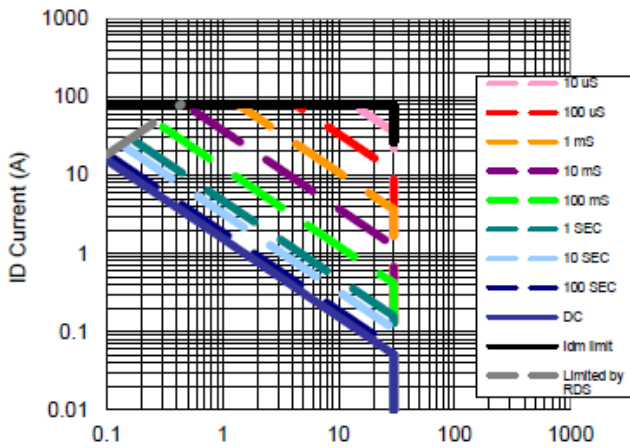
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7. Gate Charge



8. Normalized On-Resistance Vs Junction Temperature



11. Normalized Thermal Transient Junction to Ambient

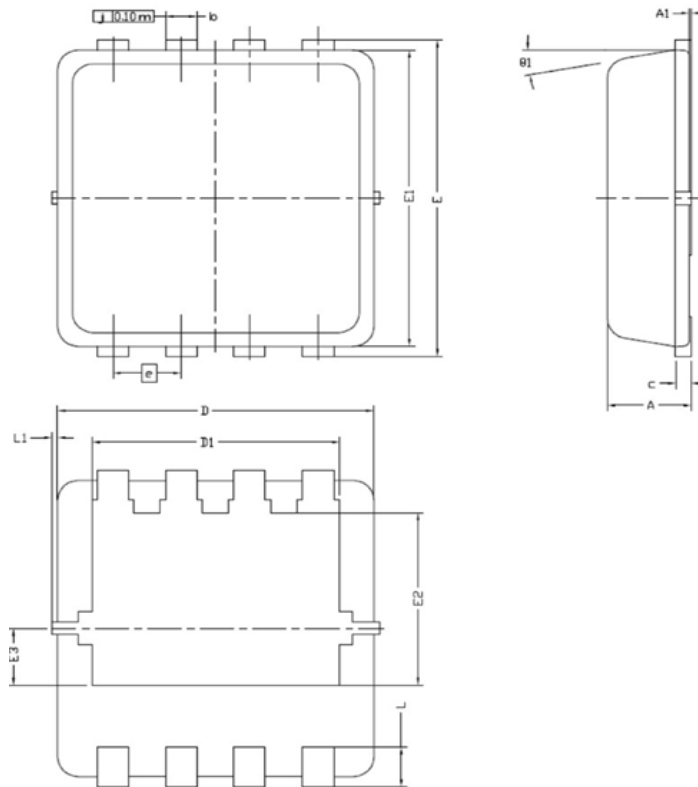


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### Packing Information

#### DFN3\*3-8L



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00		0.05	0.000		0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2.35 BSC			0.093 BSC		
E	3.20 BSC			0.126 BSC		
E1	3.00 BSC			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0.575 BSC			0.023 BSC		
e	0.65 BSC			0.026 BSC		
L	0.30	0.40	0.50	0.0118	0.0157	0.0197
L1	0		0.15	0		0.004
theta1	0°	10°	12°	0°	10°	12°



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### Notes

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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